

ABSTRACT:

The invention relates to a semiconductor device comprising a bond pad structure, which bond pad structure comprises a bond pad disposed above at least one layered structure, but preferably a stack of layered structures, wherein the layered structure comprises a metal layer and a layer of a dielectric material. In the layer of dielectric material via lines
5 are present and arranged in such a way that the metal layers and the via lines form isolated areas filled with the dielectric material.

Fig. 3

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